



ZHEJIANG UNI-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



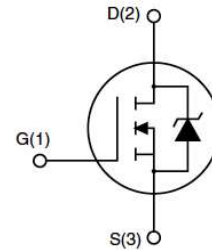
APG4015G Data Sheet

V 1.1

版权归浙江宇力微新能源科技有限公司

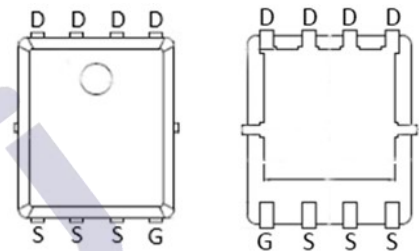
Feature

- 40V,150A
 $R_{DS(ON)} < 1.8m\Omega @ V_{GS}=10V$ (TYP:1.6m Ω)
 $R_{DS(ON)} < 3.3m\Omega @ V_{GS}=4.5V$ (TYP:2.0m Ω)
- Split Gate Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Application

- PWM applications
- Load Switch
- Power management



PDFN5X6-8L

Package Marking and Ordering Information

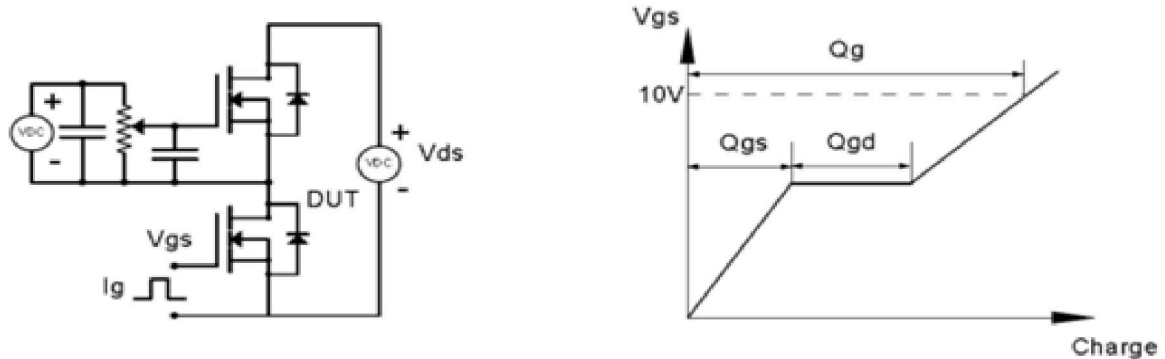
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
G4015	APG4015G	PDFN5*6-8L	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

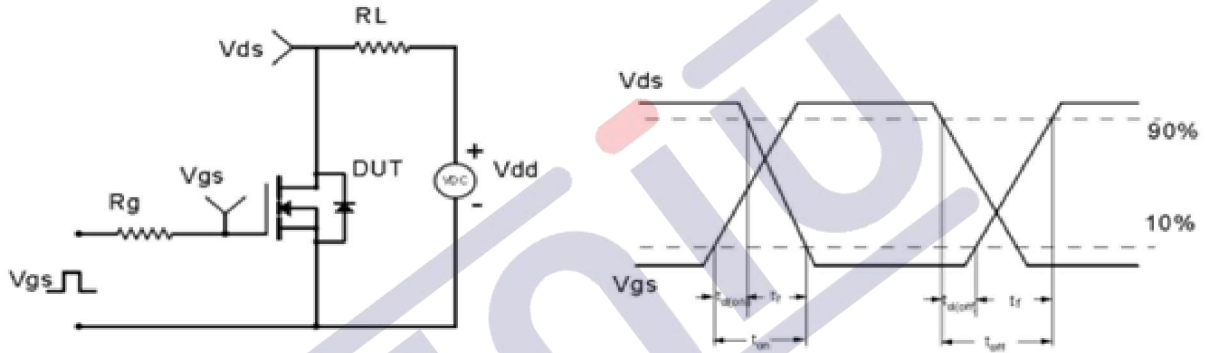
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (T _a =25°C)	I _D	150	A
Continuous Drain Current (T _a =100°C)	I _D	100	A
Pulsed Drain Current ⁽¹⁾	I _{DM}	400	A
Singel Pulsed Avalanche Energy ⁽²⁾	E _{AS}	320	mJ
Power Dissipation	P _D	89	W
Thermal Resistance from Junction to Case	R _{θJC}	1.4	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

Test Circuit & Waveform

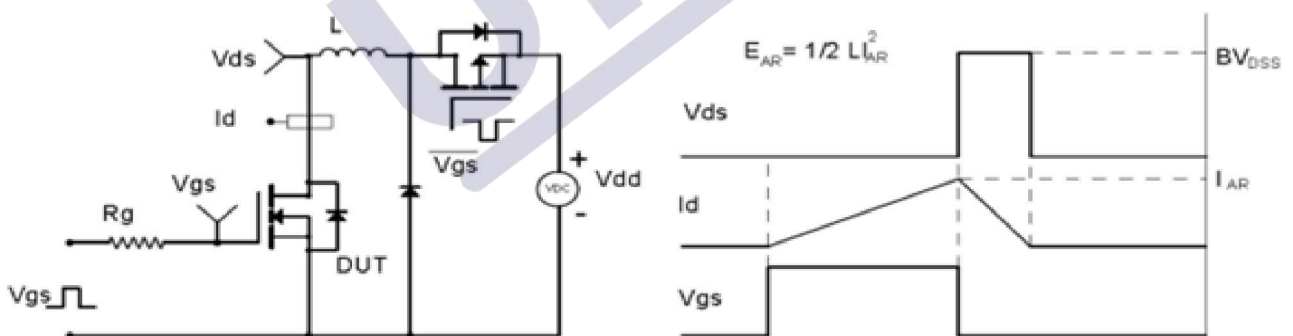
Gate Charge Test Circuit & Waveform



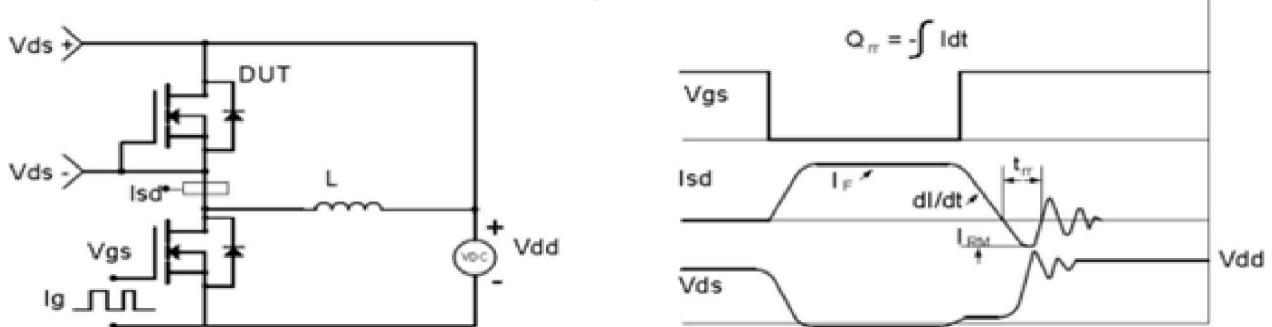
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



1.版本记录

DATE	REV.	DESCRIPTION
2018/04/19	1.0	First Release
2021/11/15	1.1	Layout adjustment

2.免责声明

浙江宇力微新能源科技有限公司保留对本文档的更改和解释权，不另行通知！客户在下单前应获取我司最新版本资料，并验证相关信息是否最新和完整。量产方案需使用方自行验证并自担所有批量风险责任。未经我司授权，该文件不得私自复制和修改。产品不断提升，以追求高品质、稳定性强、可靠性高、环保、节能、高效为目标，我司将竭诚为客户提供性价比高的系统开发方案、技术支持等更优秀的服务。

版权所有 浙江宇力微新能源科技有限公司/绍兴宇力半导体有限公司

3.联系我们

浙江宇力微新能源科技有限公司

总部地址：绍兴市越城区斗门街道袍渎路25号中节能科创园45幢4/5楼

电话：0575-85087896（研发部）

传真：0575-88125157

E-mail: htw@uni-semic.com

无锡地址：无锡市锡山区先锋中路6号中国电子（无锡）数字芯城1#综合楼503室

电话：0510-85297939

E-mail: zh@uni-semic.com

深圳地址：深圳市宝安区西乡街道南昌社区宝源路泳辉国际商务大厦410

电话：0755-84510976

E-mail: htw@uni-semic.com